

CEM8958A

30V/-30V ▲ 20mΩ/36mΩ ▲ N&P Si MOSFET

SILICON Si MOSFET ▲ SMD type

N- and P-channel enhancement mode

UL94V-0 rated flame retardant epoxy

SO8 package ▲ MSL 3

Super high dense cell density for extremely low $R_{DS(ON)}$

High power and current handling capability






MAXIMUM RATINGS

Parameter ($T_A = 25^\circ\text{C}$, unless otherwise noted)		N-Channel	P-Channel
Drain-Source Voltage	V_{DS}	30V	-30V
Gate-Source Voltage	V_{GS}	$\pm 20\text{V}$	$\pm 20\text{V}$
Continuous Drain Current at $T_A = 25^\circ\text{C}$	I_D	6.8A	-5.4A
Continuous Drain Current at $T_A = 70^\circ\text{C}$	I_D	5.4A	-4.3A
Pulsed Drain Current ^{Note 1}	I_{DM}	27A	-21A
Maximum Power Dissipation	P_D	2W	
Operating and Storage Temperature Range	T_J, T_{STG}	-55°C to +150°C	

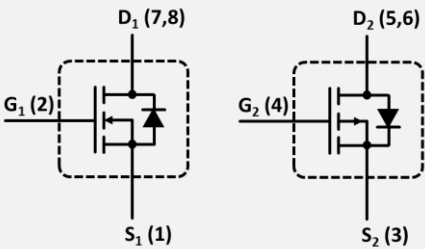
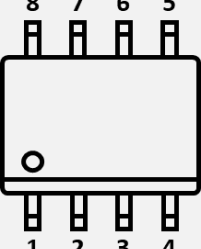
THERMAL CHARACTERISTICS

Parameter	Symbol	Limit
Thermal Resistance, Junction-to-Ambient ^{Note 2}	R_{TH_JA}	62.5°C/W
Thermal Resistance, Junction-to-Case	R_{TH_JC}	40°C/W

APPLICATIONS

Battery Pack	DC/DC Converter	High Side Switches	Low Side Switches	Power Banks
				

PIN DESCRIPTION

Circuit Diagram	Outline - Top View	Pin No.	Description
		1 2 3 4 5 6 7 8	Source MOSFET 1 Gate MOSFET 1 Source MOSFET 2 Gate MOSFET 2 Drain MOSFET 2 Drain MOSFET 2 Drain MOSFET 1 Drain MOSFET 1

N-CHANNEL ELECTRICAL CHARACTERISTICS ▲ $T_A = 25^\circ\text{C}$, unless otherwise noted

Item	Condition	Symbol	Min.	Typ.	Max.	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = 250\mu A$	BV_{DSS}	30			V
Zero Gate Voltage Drain Current	$V_{DS} = 30V, V_{GS} = 0V$	I_{DSS}			1	μA
Gate Body Leakage Current, Forward	$V_{GS} = 20V, V_{DS} = 0V$	I_{GSSF}			100	nA
Gate Body Leakage Current, Reverse	$V_{GS} = -20V, V_{DS} = 0V$	I_{GSSR}			-100	nA
On Characteristics ^{Note 3}						
Gate Threshold Voltage	$V_{GS} = V_{DS}, I_D = 250\mu A$	$V_{GS(th)}$	1		2.5	V
Static Drain-Source On-Resistance	$V_{GS} = 10V, I_D = 6.8A$	$R_{DS(ON)}$		20	28	m Ω
Static Drain-Source On-Resistance	$V_{GS} = 4.5V, I_D = 6A$	$R_{DS(ON)}$		28	42	m Ω
Dynamic Characteristics ^{Note 4}						
Input Capacitance	$V_{DS} = 15V, V_{GS} = 0V, f = 1MHz$	C_{ISS}		345		pF
Output Capacitance	$V_{DS} = 15V, V_{GS} = 0V, f = 1MHz$	C_{OSS}		105		pF
Reverse Transfer Capacitance	$V_{DS} = 15V, V_{GS} = 0V, f = 1MHz$	C_{RSS}		70		pF
Switching Characteristics ^{Note 4}						
Turn-On Delay Time	$V_{DD} = 15V, V_{GS} = 10V, I_D = 6.8A, R_{G(ext)} = 2.7\Omega$	$t_{D(ON)}$		8		ns
Turn-On Rise Time	$V_{DD} = 15V, V_{GS} = 10V, I_D = 6.8A, R_{G(ext)} = 2.7\Omega$	t_R		5		ns
Turn-Off Delay Time	$V_{DD} = 15V, V_{GS} = 10V, I_D = 6.8A, R_{G(ext)} = 2.7\Omega$	$t_{D(OFF)}$		29		ns
Turn-Off Fall Time	$V_{DD} = 15V, V_{GS} = 10V, I_D = 6.8A, R_{G(ext)} = 2.7\Omega$	t_F		8		ns
Total Gate Charge	$V_{DS} = 15V, V_{GS} = 10V, I_D = 6.8A$	Q_G		10.7		nC
Gate Source Charge	$V_{DS} = 15V, V_{GS} = 10V, I_D = 6.8A$	Q_{GS}		0.7		nC
Gate Drain Charge	$V_{DS} = 15V, V_{GS} = 10V, I_D = 6.8A$	Q_{GD}		3.3		nC
Drain-Source Diode Characteristics and Maximum Ratings						
Drain-Source Diode Forward Current ^{Note 2}		I_S			1.3	A
Drain-Source Diode Forward Voltage ^{Note 3}	$V_{GS} = 0V, I_S = 1.3A$	V_{SD}			1.2	V

Notes

- 1: Repetitive Rating: Pulse width limited by maximum junction temperature
- 2: Surface Mounted on FR4 Board, $t \leq 10$ sec
- 3: Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$.
- 4: Guaranteed by design, not subject to production testing.

P-CHANNEL ELECTRICAL CHARACTERISTICS ▲ $T_A = 25^\circ\text{C}$, unless otherwise noted

Item	Condition	Symbol	Min.	Typ.	Max.	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = 250\mu A$	BV_{DSS}	-30			V
Zero Gate Voltage Drain Current	$V_{DS} = -30V, V_{GS} = 0V$	I_{DSS}			-1	μA
Gate Body Leakage Current, Forward	$V_{GS} = 20V, V_{DS} = 0V$	I_{GSSF}			100	nA
Gate Body Leakage Current, Reverse	$V_{GS} = -20V, V_{DS} = 0V$	I_{GSSR}			-100	nA
On Characteristics ^{Note 3}						
Gate Threshold Voltage	$V_{GS} = V_{DS}, I_D = -250\mu A$	$V_{GS(th)}$	-1		-2.5	V
Static Drain-Source On-Resistance	$V_{GS} = -10V, I_D = -4.8A$	$R_{DS(ON)}$		36	45	m Ω
Static Drain-Source On-Resistance	$V_{GS} = -4.5V, I_D = -3.5A$	$R_{DS(ON)}$		60	80	m Ω
Dynamic Characteristics ^{Note 4}						
Input Capacitance	$V_{DS} = -15V, V_{GS} = 0V, f = 1MHz$	C_{ISS}		675		pF
Output Capacitance	$V_{DS} = -15V, V_{GS} = 0V, f = 1MHz$	C_{OSS}		120		pF
Reverse Transfer Capacitance	$V_{DS} = -15V, V_{GS} = 0V, f = 1MHz$	C_{RSS}		75		pF
Switching Characteristics ^{Note 4}						
Turn-On Delay Time	$V_{DD} = -15V, V_{GS} = -10V, I_D = -1A, R_{G(ext)} = 6\Omega$	$t_{D(ON)}$		12		ns
Turn-On Rise Time	$V_{DD} = -15V, V_{GS} = -10V, I_D = -1A, R_{G(ext)} = 6\Omega$	t_R		4		ns
Turn-Off Delay Time	$V_{DD} = -15V, V_{GS} = -10V, I_D = -1A, R_{G(ext)} = 6\Omega$	$t_{D(OFF)}$		54		ns
Turn-Off Fall Time	$V_{DD} = -15V, V_{GS} = -10V, I_D = -1A, R_{G(ext)} = 6\Omega$	t_F		9		ns
Total Gate Charge	$V_{DD} = -15V, V_{GS} = -10V, I_D = -3.2A$	Q_G		11.5		nC
Gate Source Charge	$V_{DD} = -15V, V_{GS} = -10V, I_D = -3.2A$	Q_{GS}		1.3		nC
Gate Drain Charge	$V_{DD} = -15V, V_{GS} = -10V, I_D = -3.2A$	Q_{GD}		2.3		nC
Drain-Source Diode Characteristics and Maximum Ratings						
Drain-Source Diode Forward Current ^{Note 2}		I_S			-1.3	A
Drain-Source Diode Forward Voltage ^{Note 3}	$V_{GS} = 0V, I_S = -1.3A$	V_{SD}			-1.2	V

Notes

- 1: Repetitive Rating: Pulse width limited by maximum junction temperature
- 2: Surface Mounted on FR4 Board, $t \leq 10$ sec
- 3: Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$.
- 4: Guaranteed by design, not subject to production testing.

N-CHANNEL REFERENCE DATA ▲ TYPICAL DEVICE PERFORMANCE

Fig. 1 • Output Characteristics

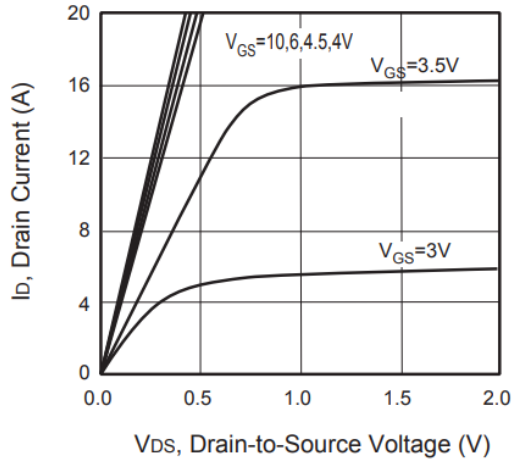


Fig. 2 • Transfer Characteristics

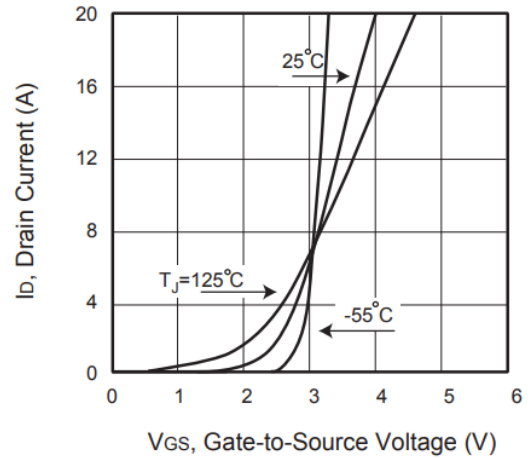


Fig. 3 • Capacitance

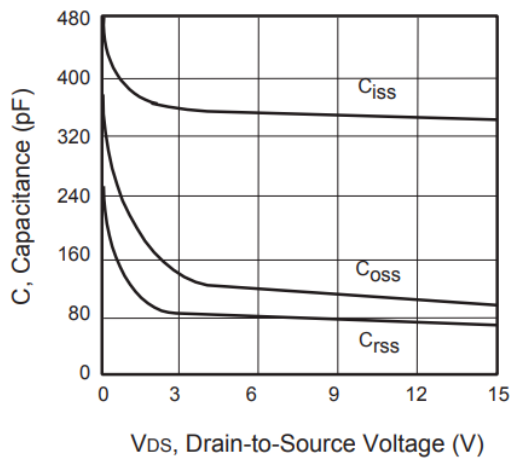


Fig. 4 • On-Resistance Variation with Temperature

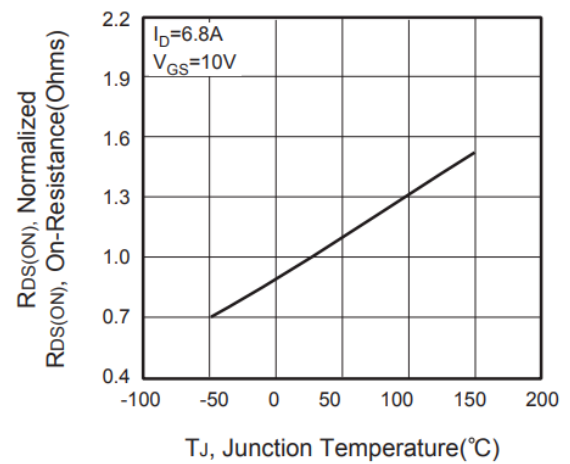


Fig. 5 • Gate Threshold Variation with Temperature

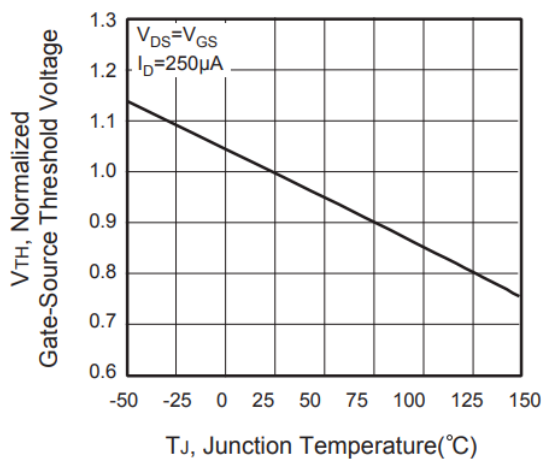
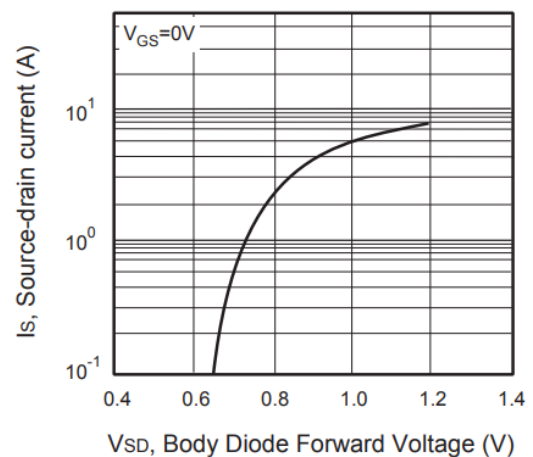


Fig. 6 • Body Diode Forward Voltage Variation with Source Current



P-CHANNEL REFERENCE DATA ▲ TYPICAL DEVICE PERFORMANCE

Fig. 7 • Output Characteristics

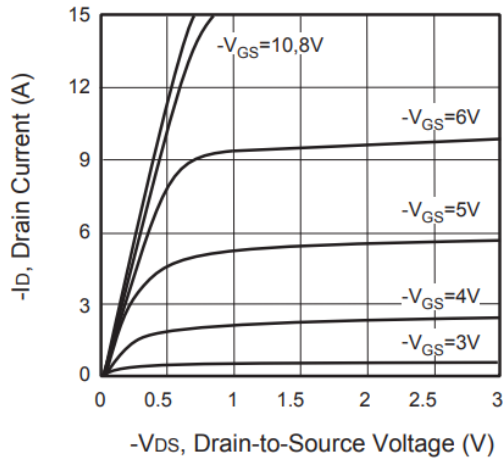


Fig. 8 • Transfer Characteristics

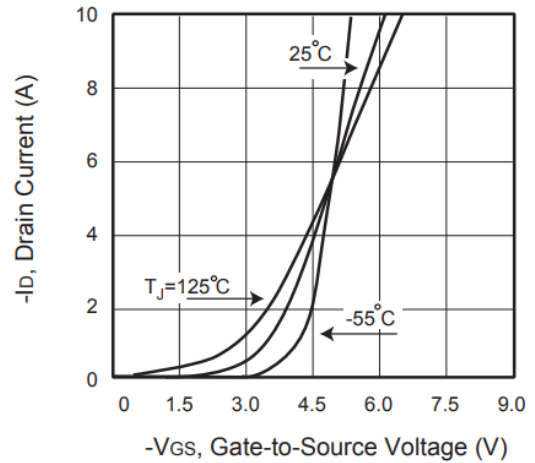


Fig. 9 • Capacitance

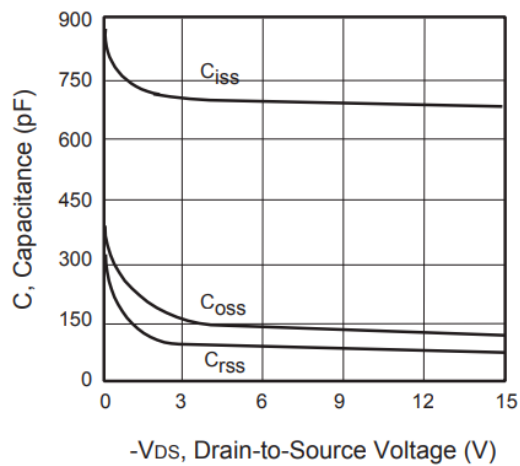


Fig. 10 • On-Resistance Variation with Temperature

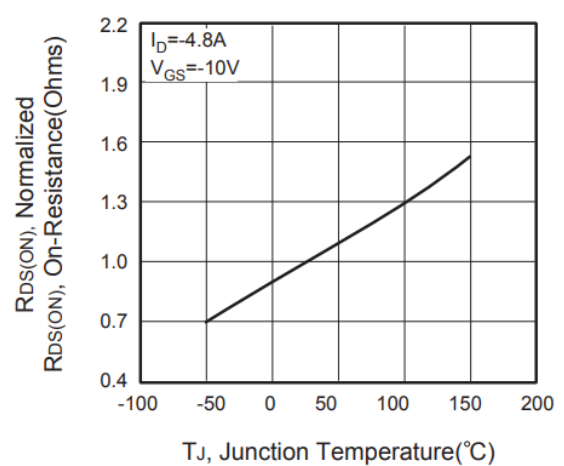


Fig. 11 • Gate Threshold Variation with Temperature

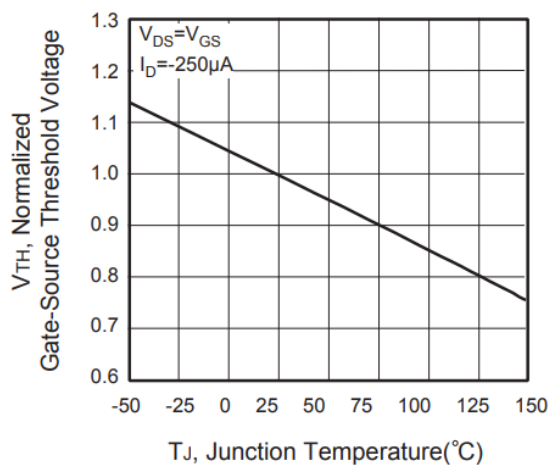
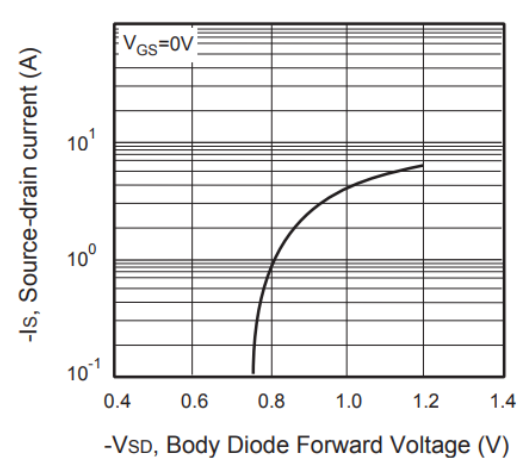


Fig. 12 • Body Diode Forward Voltage Variation with Source Current



N-CHANNEL REFERENCE DATA ▲ TYPICAL DEVICE PERFORMANCE

Fig. 13 • Gate Charge

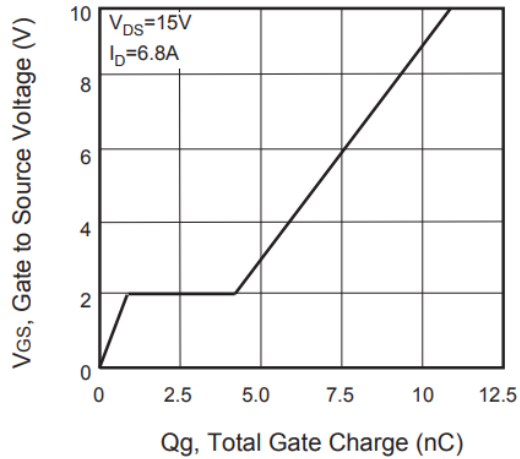
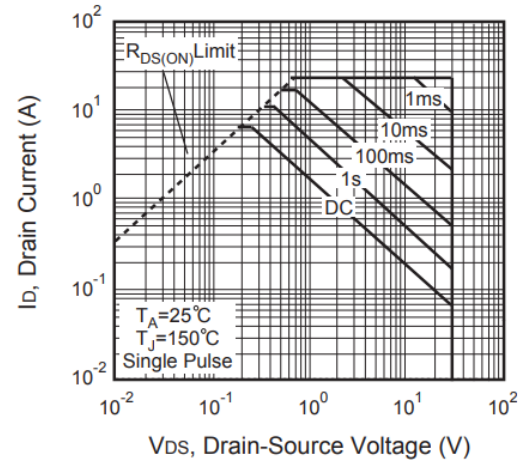


Fig. 14 • Maximum Safe Operating Area



P-CHANNEL ▲ REFERENCE DATA ▲ TYPICAL DEVICE PERFORMANCE

Fig. 15 • Gate Charge

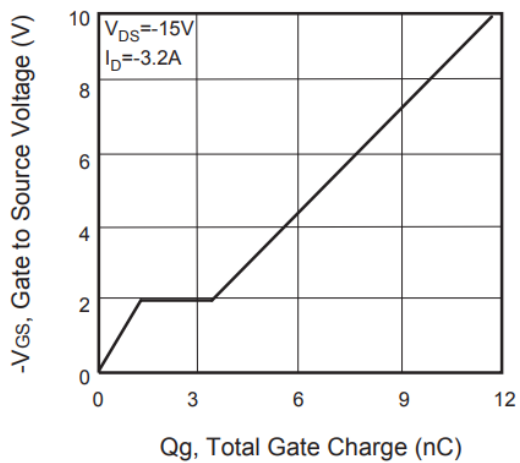
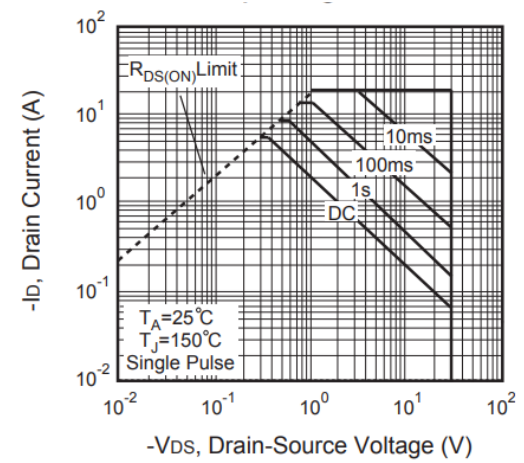


Fig. 16 • Maximum Safe Operating Area



REFERENCE DATA ▲ TYPICAL DEVICE PERFORMANCE

Fig. 17 • Switching Test Circuit

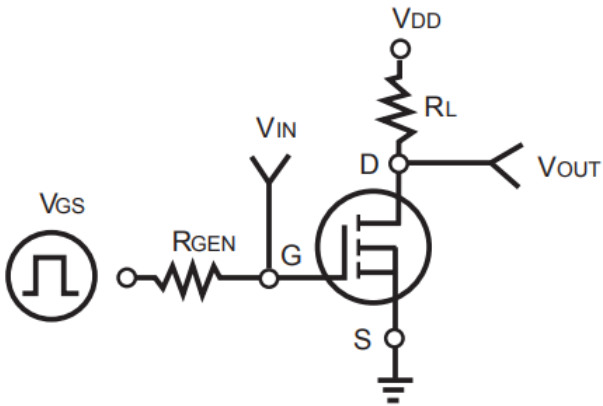


Fig. 18 • Switching Waveforms

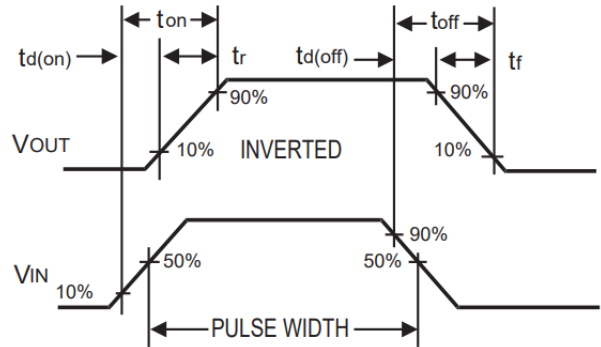
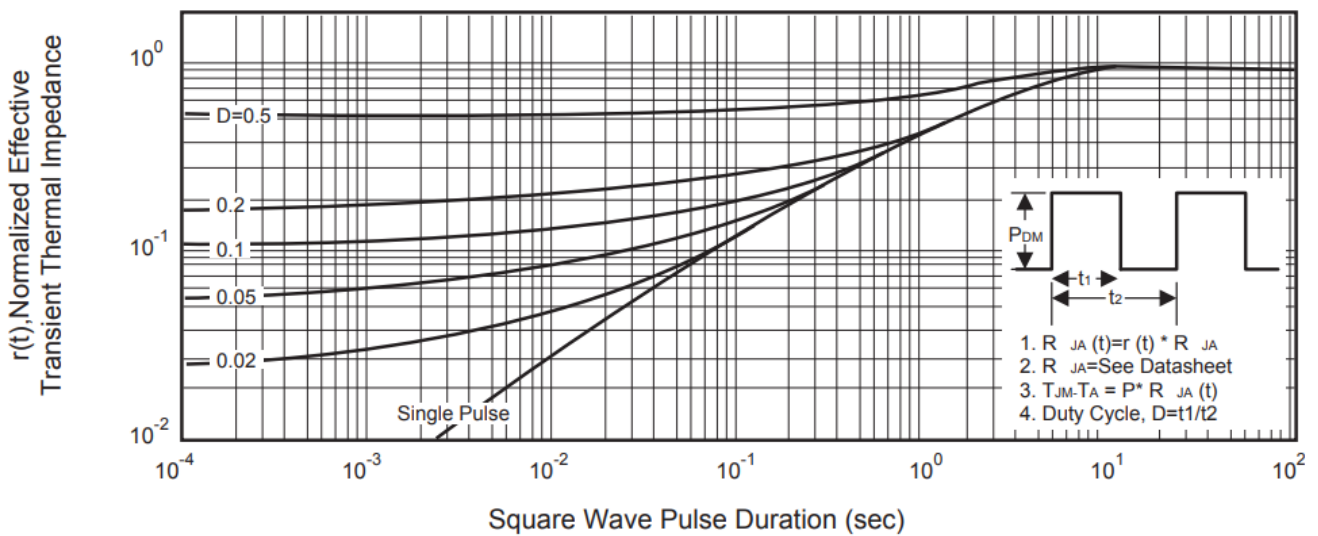
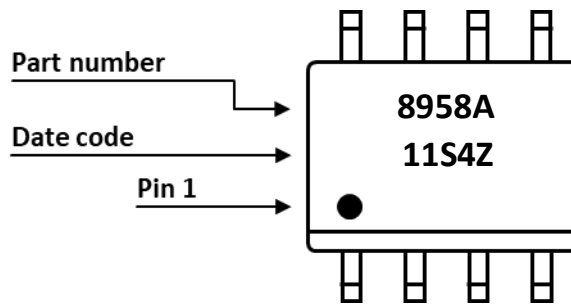


Fig. 19 • Normalized Thermal Transient Impedance Curve

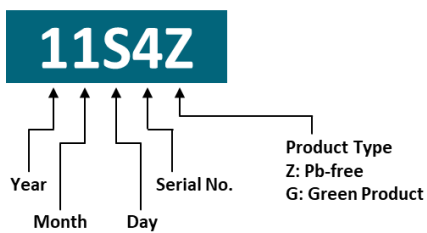


PART MARKING



DATE CODE

Example: 11S4Z



Coding list for „Day“

1	2	3	4	5	6	7	8	9	A
01	02	03	04	05	06	07	08	09	10
B	C	D	E	F	G	H	I	J	K
11	12	13	14	15	16	17	18	19	20
L	M	N	O	P	Q	R	S	T	U
21	22	23	24	25	26	27	28	29	30
V									
31									

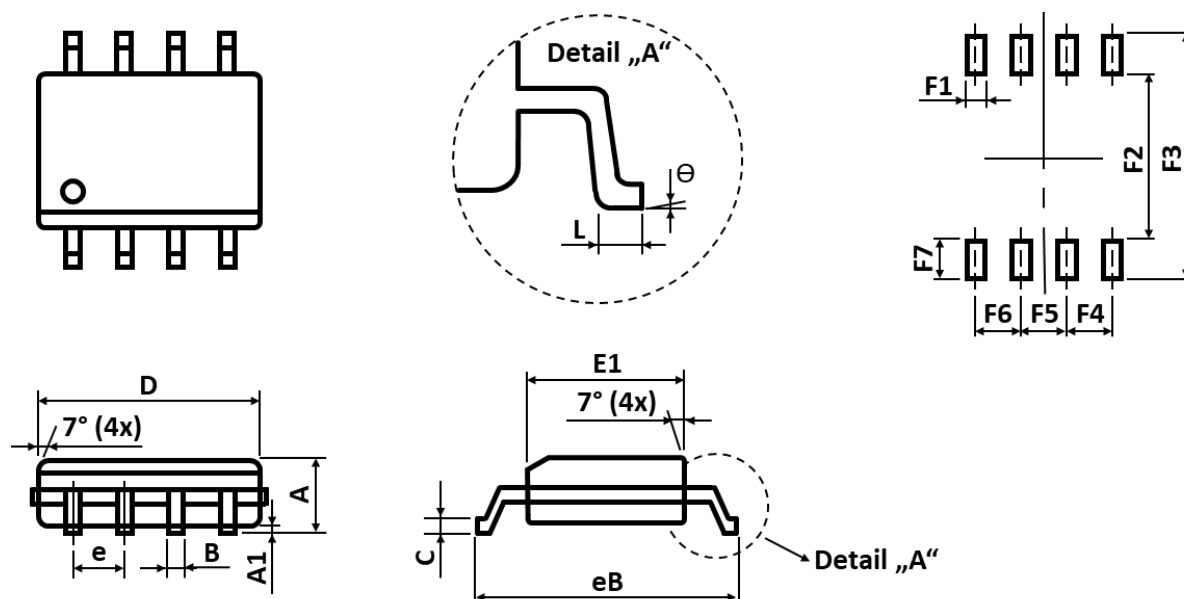
Coding list for „Month“

1	2	3	4	5	6
Jan	Feb	Mar	Apr	May	Jun
7	8	9	A	B	C
Jul	Aug	Sep	Oct	Nov	Dec

Coding list for „Year“

0	1	2	3	4
2020	2021	2022	2023	2024
5	6	7	8	9
2025	2026	2027	2028	2029

PACKAGE OUTLINE AND RECOMMENDED PAD LAYOUT



Sym	Millimeters (Min.)	Millimeters (Typ.)	Millimeters (Max.)
A	1.350	-	1.750
A1	0.100	-	0.250
B	0.310	-	0.510
C	0.170	-	0.250
D	4.690	-	5.000

Sym	Millimeters (Min.)	Millimeters (Typ.)	Millimeters (Max.)
F1	-	0.500	-
F2	-	4.250	-
F3	-	6.250	-
F4	-	1.270	-

Sym	Millimeters (Min.)	Millimeters (Typ.)	Millimeters (Max.)
E1	3.700	-	4.060
eB	5.800	-	6.200
e	-	1.270	-
L	0.400	-	0.950
θ	0°	-	8°

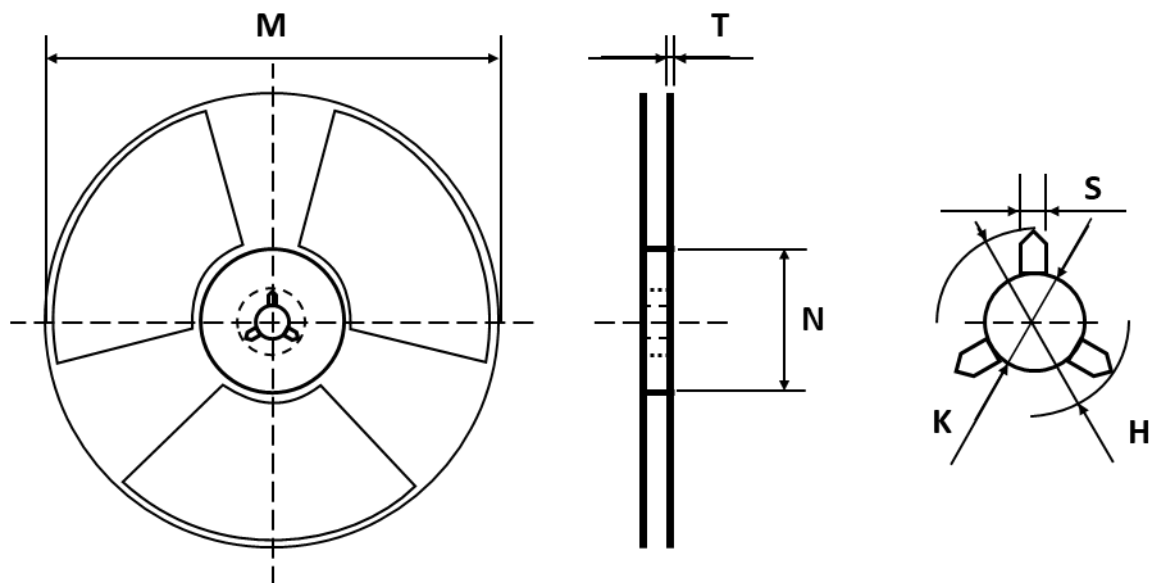
Sym	Millimeters (Min.)	Millimeters (Typ.)	Millimeters (Max.)
F5	-	1.270	-
F6	-	1.270	-
F7	-	1.000	-

- Notes: 1. The suggested land pattern dimensions have been provided for reference only.
2. For further information, please reference document IPC-7351A.

ORDERING INFORMATION

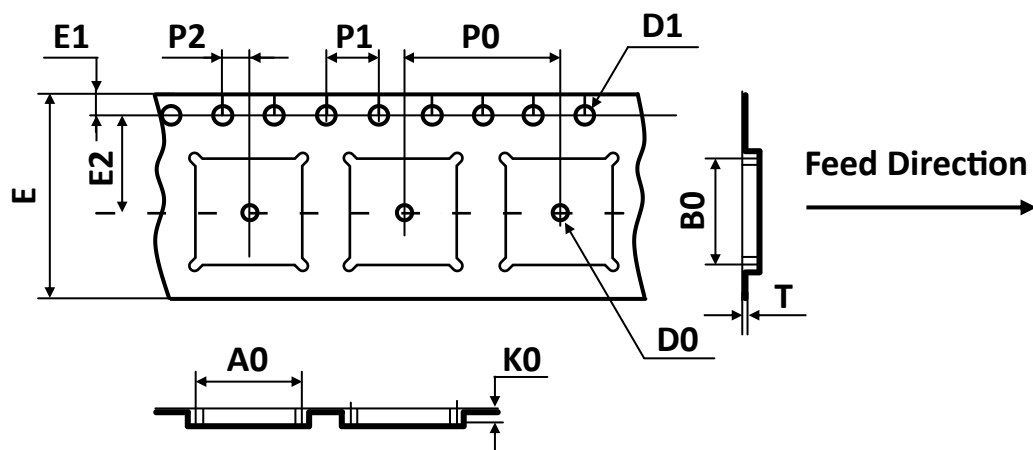
Part Number	Package	Packing	Reel Qty.	Inner Box Qty.	Outer Box Qty.
CEM8958A	SO8	13" Reel	2,500pcs	5,000pcs	40,000pcs

REEL DIMENSIONS ▲ All dimensions in mm



Tape Size	Reel Size	M	N	T	H	K	S
12mm	Ø330	Ø330.00 ±2.00	Ø100.00 ±0.50	2.20 ±0.20	20.00 ±1.00	13.20 ±0.20	3.00 ±1.00

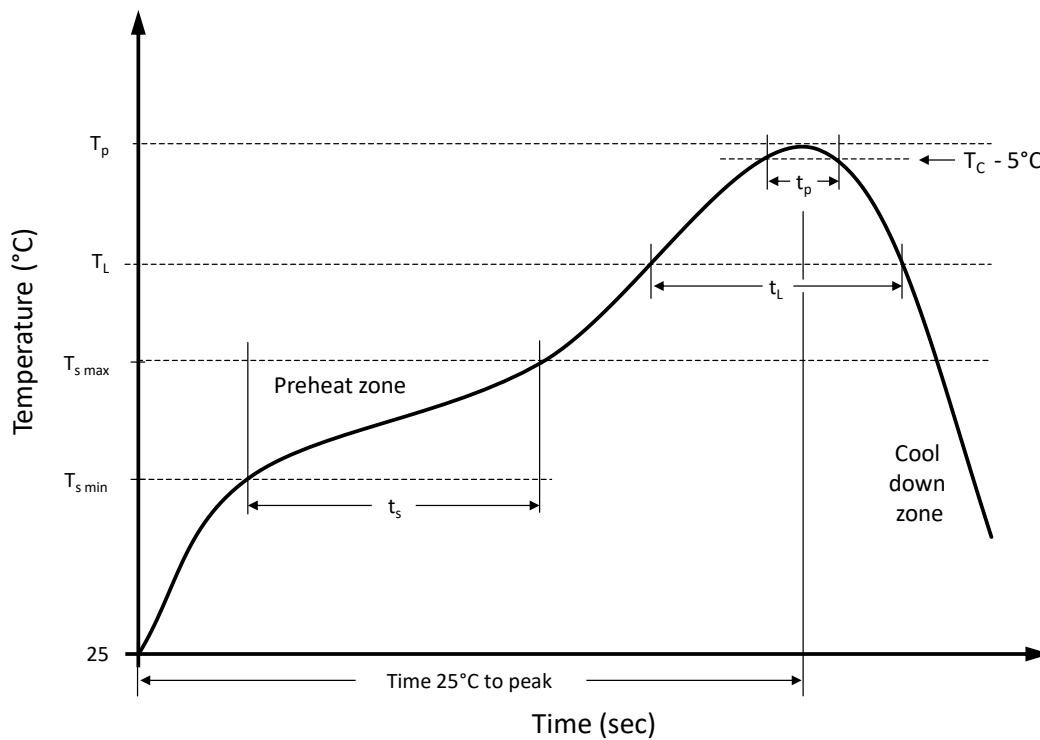
TAPE DIMENSIONS ▲ All dimensions in mm



Package	A0	B0	K0	D0	D1	E	E1	E2	P0	P1	P2	T
SO8	6.50 ±0.10	5.30 ±0.10	2.05 ±0.15	1.50 ±0.10	1.50 ±0.10	12.00 ±0.10	1.75 ±0.10	5.50 ±0.10	8.00 ±0.10	4.00 ±0.10	2.00 ±0.05	0.25 ±0.02

Note: All dimensions meet EIA-481-D requirements.

RECOMMENDED REFLOW SOLDERING PROFILE



Recommended reflow soldering conditions ▲ Refer to JEDEC J-STD-020E

Profile Features		Sn-Pb Eutetic Assembly	Pb-Free Assembly
Preheat temperature min.	$T_{s \min}$	100 °C	150 °C
Preheat temperature max.	$T_{s \max}$	150 °C	200 °C
Preheat time t_s from $T_{s \min}$ to $T_{s \max}$	t_s	120 seconds	120 seconds
Ramp-up rate (T_L to T_p)		max. 3 °C/second	max. 3 °C/second
Liquidous temperature	T_L	183 °C	217 °C
Time t_L maintained above T_L	t_L	150 seconds max.	150 seconds max.
Peak package body temperature	T_p	235°C	260°C
Timeframe of within 5°C below and up to max actual peak body temperature	t_p	20 seconds max.	30 seconds max.
Ramp-down rate (T_L to T_p)		max. 6 °C/second	max. 6 °C/second
Time 25°C to peak temperature		max. 6 minutes	max. 8 minutes

REVISION TABLE

Revision	Date	Status	Notes
001	30/09/2022	Initial release	Initial publication

DISCLAIMER

Except for the written expressed warranties, MGT does not implicitly, by assumption or whatever else, warrant, under-take, promise any other warranty or guaranty for any MGT product.

All information and technical specifications made available by MGT are for guidance only and we reserve the right to change or modify them without prior notice. Unless expressly stated in writing by MGT, we reject any guarantees, obligations, or warranties.

All MGT products with the technical specifications described are suitable for use in certain applications. Operating, production, storage and environmental conditions can have a massive influence on the parameters mentioned in the data sheets, which cause the performance to vary over time.

It is subject to the user's duty of care to design and validate his products in such a way that appropriate measures are taken, such as protective circuits or redundant systems to ensure the safety standards required in the application.

MGT components are not designed or rated for use in life support, rescue, safety critical, military, or aerospace applications where failure or malfunction could result in property or environmental damage, serious injury or death. In the aforementioned cases, please contact us before using MGT products.

In principle, we reserve all rights and MGT's general terms and conditions apply. You can find them on our website www.mgt.co.com.